

Hiroshi Inokawa

List of Publications by Year in descending order

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162
papers

2,847
citations

218677

26
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197818

49
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164
all docs

164
docs citations

164
times ranked

1969
citing authors

#	ARTICLE	IF	CITATIONS
1	FDTD Study on Evolution of Trimer Silver@Silica Nanospheres to Dimer for SERS Characteristics. Plasmonics, 2022, 17, 647-652.	3.4	3
2	High-frequency rectifying characteristics of metallic single-electron transistor with niobium nanodots. Japanese Journal of Applied Physics, 2022, 61, SC1063.	1.5	4
3	Responsivity and NEP Improvement of Terahertz Microbolometer by High-Impedance Antenna. Sensors, 2022, 22, 5107.	3.8	3
4	Noncontact Characterization Techniques of GaN-Based Terahertz Devices. Lecture Notes in Electrical Engineering, 2021, , 29-42.	0.4	0
5	Design and Development of Terahertz Medical Screening Devices. Lecture Notes in Electrical Engineering, 2021, , 395-404.	0.4	4
6	Terahertz Radiation from Gallium Phosphide Avalanche Transit Time Sources. , 2021, , 49-58.		1
7	Tunable graphene nanopatch antenna design for on-chip integrated terahertz detector arrays with potential application in cancer imaging. Nanomedicine, 2021, 16, 1035-1047.	3.3	19
8	Real-time FPGA-based signal processing for silicon-on-insulator MOSFET single-photon detector: study on photon number statistics. Japanese Journal of Applied Physics, 2021, 60, 092004.	1.5	1
9	Measurement of thermal conductivity and thermal diffusivity of one-dimensional-system material by scanning electron microscopy and infrared thermography. AIP Advances, 2021, 11, .	1.3	1
10	Substrate Bias Effect on SOI-based Thermoelectric Power Generator. , 2021, , .		0
11	Responsivity Calibration of Terahertz Pyroelectric Detector Based on Blackbody Radiator. , 2021, , .		0
12	Angle-Sensitive Detector Based on Silicon-On-Insulator Photodiode Stacked with Surface Plasmon Antenna. Sensors, 2020, 20, 5543.	3.8	6
13	Polarization Dependence Of Incident Angle Sensitivity In Soi Photodiode With 2d Hole Array Grating. , 2020, , .		0
14	Performance Comparison of SOI-Based Temperature Sensors for Room-Temperature Terahertz Antenna-Coupled Bolometers: MOSFET, PN Junction Diode and Resistor. Micromachines, 2020, 11, 718.	2.9	12
15	Angular selectivity of SOI photodiode with surface plasmon antenna. IEICE Electronics Express, 2020, 17, 20200187-20200187.	0.8	5
16	Investigation of silicon-on-insulator CMOS integrated thermocouple and heater for antenna-coupled bolometer. Japanese Journal of Applied Physics, 2019, 58, SDDE08.	1.5	2
17	Performance improvement of on-chip integrable terahertz microbolometer arrays using nanoscale meander titanium thermistor. Journal of Applied Physics, 2019, 125, .	2.5	21
18	Synthesis of Triâ€functional Coreâ€shell CuO@carbon Quantum Dots@carbon Hollow Nanospheres Heterostructure for Nonâ€enzymatic H ₂ O ₂ Sensing and Overall Water Splitting Applications. Electroanalysis, 2019, 31, 2120-2129.	2.9	6

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19	Development of carbon coated NiS ₂ as positive electrode material for high performance asymmetric supercapacitor. Composites Part B: Engineering, 2019, 177, 107373.	12.0	72
20	Optimization of electric field enhancement of Ag@SiO ₂ trimer nanospheres by finite difference time domain method. Applied Surface Science, 2019, 495, 143547.	6.1	12
21	Optimization of active surface area of flower like MoS ₂ using V-doping towards enhanced hydrogen evolution reaction in acidic and basic medium. Applied Catalysis B: Environmental, 2019, 254, 432-442.	20.2	185
22	Directivity of SOI Photodiode with Gold Surface Plasmon Antenna. , 2019, , .		1
23	Comparative Study on 1-THz Antenna-Coupled Bolometer with Various SOI-CMOS based Temperature Sensors: MOSFET, Diode, Resistor and Thermocouple. , 2019, , .		0
24	Impact of Downscaling on Terahertz Antenna-Coupled Bolometers. , 2019, , .		2
25	Room-Temperature Terahertz Antenna-Coupled Microbolometers with Titanium Thermistor and Heater. , 2019, , .		1
26	High Responsivity and Low NEP of Room-Temperature Terahertz Antenna-Coupled Microbolometers with Meander Titanium Thermistor. , 2019, , .		2
27	A SILAR method for the fabrication of layer-by-layer assembled Cu ₂ O-reduced graphene oxide composite for non-enzymatic detection of hydrogen peroxide. Materials Research Express, 2019, 6, 025045.	1.6	4
28	Optimization of narrow width effect on titanium thermistor in uncooled antenna-coupled terahertz microbolometer. Japanese Journal of Applied Physics, 2018, 57, 04FC09.	1.5	16
29	Modified electrochemical charge storage properties of h-BN/rGO superlattice through the transition from n to p type semiconductor by fluorine doping. Chemical Engineering Journal, 2018, 339, 334-345.	12.7	27
30	Characterization of platinum and titanium thermistors for terahertz antenna-coupled bolometer applications. Sensors and Actuators A: Physical, 2018, 273, 49-57.	4.1	24
31	Novel synthesis of a Cu ₂ O-graphene nanoplatelet composite through a two-step electrodeposition method for selective detection of hydrogen peroxide. New Journal of Chemistry, 2018, 42, 3574-3581.	2.8	21
32	Modeling, Simulation, Fabrication, and Characterization of a 10 ⁴ W/cm ² Class Si-Nanowire Thermoelectric Generator for IoT Applications. IEEE Transactions on Electron Devices, 2018, 65, 5180-5188.	3.0	54
33	10 ⁴ W/cm ² -Class High Power Density Planar Si-Nanowire Thermoelectric Energy Harvester Compatible with CMOS-VLSI Technology. , 2018, , .		7
34	Antenna-Coupled Terahertz Microbolometers with Meander Structures: the Comparison of Titanium and Platinum Thermistors. , 2018, , .		3
35	Ultrahigh-Frequency Characteristics of Single-Electron Transistor. , 2018, , .		6
36	Application of bow-tie surface plasmon antenna to silicon on insulator nanowire photodiode for enhanced light absorption. IEICE Electronics Express, 2018, 15, 20180328-20180328.	0.8	3

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37	1.0 THz GaN IMPATT Source: Effect of Parasitic Series Resistance. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2018, 39, 954-974.	2.2	39
38	Width dependence of platinum and titanium thermistor characteristics for application in room-temperature antenna-coupled terahertz microbolometer. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CC07.	1.5	21
39	Thermal conductance and heat capacity measurement utilizing suspended-wire resistor. , 2017, , .		0
40	Strong Quantum Confinement Effects in Nanometer Devices with Graphene Directly Grown on Insulator by Catalyst-free Chemical Vapor Deposition. <i>Current Graphene Science</i> , 2017, 1, .	0.5	0
41	Highly sensitive and functional photodetectors based on silicon-on-insulator. , 2016, , .		1
42	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	6
43	Fabrication and analytical modeling of integrated heater and thermistor for antenna-coupled bolometers. <i>Sensors and Actuators A: Physical</i> , 2015, 222, 160-166.	4.1	17
44	Room-temperature THz antenna-coupled microbolometer with a Joule-heating resistor at the center of a half-wave antenna. , 2014, , .		10
45	Broadband absorption enhancement of thin SOI photodiode with high-density gold nanoparticles. <i>Optical Materials Express</i> , 2014, 4, 725.	3.0	6
46	Effects of substrate voltage on noise characteristics and hole lifetime in SOI metal-oxide-semiconductor field-effect transistor photon detector. <i>Optics Express</i> , 2014, 22, 22072.	3.4	2
47	Material Dependence of Metal Grating on SOI Photodiode for Enhanced Quantum Efficiency. <i>IEEE Photonics Technology Letters</i> , 2013, 25, 1133-1136.	2.5	9
48	Evolution of photodetectors by silicon-on-insulator material. , 2013, , .		0
49	Substrate bias effects on noise and minority carrier lifetime in SOI MOSFET single-photon detector. , 2013, , .		0
50	Enhanced Visible Light Sensitivity by Gold Line-and-Space Grating Gate Electrode in Thin Silicon-On-Insulator p-n Junction Photodiode. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 812-818.	3.0	12
51	Enhancement of SOI Photodiode Sensitivity by Aluminum Grating. <i>ECS Transactions</i> , 2013, 53, 127-130.	0.5	4
52	(Invited) High-Speed Operation of Si Single-Electron Transistor. <i>ECS Transactions</i> , 2013, 58, 73-80.	0.5	4
53	Analysis of Hole Lifetime in SOI MOSFET Single-Photon Detector. <i>MAKARA of Technology Series</i> , 2013, 17, .	0.0	0
54	Single-Photon Detection by a Simple Silicon-on-Insulator Metal-oxide-Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 06FE01.	1.5	5

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55	Effect of Arrangement of Input Gates on Logic Switching Characteristics of Nanodot Array Device. IEICE Transactions on Electronics, 2012, E95.C, 865-870.	0.6	2
56	High-frequency properties of Si single-electron transistor. , 2012, , .		1
57	Optoelectrical lifetime evaluation of single holes in SOI MOSFET. , 2012, , .		0
58	A differential smoothing technique for the extraction of MOSFET threshold voltage using extrapolation in the linear region. Solid-State Electronics, 2012, 76, 5-7.	1.4	9
59	Surface Plasmon Antenna with Gold Line and Space Grating for Enhanced Visible Light Detection by a Silicon-on-Insulator Metalâ€“Oxideâ€“Semiconductor Photodiode. IEEE Nanotechnology Magazine, 2012, 11, 346-351.	2.0	12
60	Single-Photon Detection by a Simple Silicon-on-Insulator Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2012, 51, 06FE01.	1.5	6
61	Single-photon detection by SOI MOSFET. , 2011, , .		0
62	SOI metal-oxide-semiconductor field-effect transistor photon detector based on single-hole counting. Optics Letters, 2011, 36, 2800.	3.3	16
63	è¸¸éfã—ãf©ã,°ãfãf³ã,¹ã`©ç”ã—ãÿã...%æœªã†ãª™”ã®æSèf1/2ãã,Š. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan		0
64	Electrical Characterization of Terphenyl-Based Molecular Devices. Japanese Journal of Applied Physics, 2011, 50, 071603.	1.5	0
65	Sensitivity improvement of silicon-on-insulator photodiode by gold nanoparticles with substrate bias control. Applied Physics Letters, 2011, 99, .	3.3	7
66	Si Nanodot Device Fabricated by Thermal Oxidation and their Applications. Key Engineering Materials, 2011, 470, 175-183.	0.4	0
67	Single-Photon Detector Based on MOSFET Electrometer with Single-Electron Sensitivity. Advanced Materials Research, 2011, 222, 3-7.	0.3	2
68	Electrical Characterization of Terphenyl-Based Molecular Devices. Japanese Journal of Applied Physics, 2011, 50, 071603.	1.5	1
69	Fabrication of double-dot single-electron transistor in silicon nanowire. Thin Solid Films, 2010, 518, S186-S189.	1.8	7
70	Evaluation of adhesion materials for gold line-and-space surface plasmon antenna on SOI-MOS photodiode. , 2010, , .		2
71	Effect of oxide thickness on the low-frequency noise in MOSFET-based charge transfer devices. , 2010, , .		1
72	Fabrication Method of Sub-100 nm Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor with Thick Gate Oxide. Japanese Journal of Applied Physics, 2010, 49, 128002.	1.5	4

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73	Low Frequency Noise Characterization in Metal Oxide Semiconductor Field Effect Transistor Based Charge Transfer Device at Room and Low Temperatures. Japanese Journal of Applied Physics, 2010, 49, 034203.	1.5	2
74	Geometrical effect in submicrometer channel organic field effect transistors. Thin Solid Films, 2009, 518, 579-582.	1.8	1
75	Single-Electron Device With Si Nanodot Array and Multiple Input Gates. IEEE Nanotechnology Magazine, 2009, 8, 535-541.	2.0	13
76	Electromagnetic testing and image reconstruction with flexible scanning tablets. , 2009, , .		1
77	Silicon Single-Electron Devices. Nanostructure Science and Technology, 2009, , 125-172.	0.1	23
78	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. International Journal of Nanotechnology and Molecular Computation, 2009, 1, 58-69.	0.3	2
79	Charge transport in boron-doped nano MOSFETs: Towards single-dopant electronics. Applied Surface Science, 2008, 254, 6252-6256.	6.1	6
80	Silicon nanodot-array device with multiple gates. Materials Science in Semiconductor Processing, 2008, 11, 175-178.	4.0	5
81	Silicon single-charge transfer devices. Journal of Physics and Chemistry of Solids, 2008, 69, 702-707.	4.0	2
82	Pauli-spin-blockade transport through a silicon double quantum dot. Physical Review B, 2008, 77, .	3.2	115
83	Enhancement of light absorption by Au L/S grating for thin SOI photodetector. , 2008, , .		0
84	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8305-8310.	1.5	30
85	Full adder operation based on Si nanodot array device. , 2008, , .		0
86	Why the long-term charge offset drift in Si single-electron tunneling transistors is much smaller (better) than in metal-based ones: Two-level fluctuator stability. Journal of Applied Physics, 2008, 104, .	2.5	43
87	A gate-defined silicon quantum dot molecule. Applied Physics Letters, 2008, 92, 222104.	3.3	33
88	Stochastic data processing circuit based on single electrons using nanoscale field-effect transistors. Applied Physics Letters, 2008, 92, 062105.	3.3	22
89	Direct Measurement of Capacitance Parameters in Nanometer-Scale MOSFETs. IEEJ Transactions on Electronics, Information and Systems, 2008, 128, 905-911.	0.2	0
90	Field-Effect Transistor with Deposited Graphite Thin Film. Japanese Journal of Applied Physics, 2007, 46, 2615-2617.	1.5	4

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91	Long Retention of Gain-Cell Dynamic Random Access Memory With Undoped Memory Node. IEEE Electron Device Letters, 2007, 28, 48-50.	3.9	6
92	Effect of UV/Ozone Treatment on Nanogap Electrodes for Molecular Devices. Japanese Journal of Applied Physics, 2007, 46, 1731-1733.	1.5	3
93	Infrared detection with silicon nano-field-effect transistors. Applied Physics Letters, 2007, 90, 223108.	3.3	17
94	Charge offset stability in tunable-barrier Si single-electron tunneling devices. Applied Physics Letters, 2007, 90, 033507.	3.3	34
95	Mechanism of metal-semiconductor transition in electric properties of single-walled carbon nanotubes induced by low-energy electron irradiation. Journal of Applied Physics, 2007, 101, 034317.	2.5	27
96	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. Applied Physics Letters, 2007, 90, 102106.	3.3	90
97	Impact of Space-Energy Correlation on Variable Range Hopping in a Transistor. Physical Review Letters, 2007, 98, 166601.	7.8	4
98	Quantized electron transfer through random multiple tunnel junctions in phosphorus-doped silicon nanowires. Physical Review B, 2007, 76, .	3.2	54
99	Fast all-optical switching using ion-implanted silicon photonic crystal nanocavities. Applied Physics Letters, 2007, 90, 031115.	3.3	155
100	Resistance Ridges Along Filling Factor $\hat{1}/2 = 4i$ in SiO ₂ /Si/SiO ₂ Quantum Wells. AIP Conference Proceedings, 2007, , .	0.4	0
101	Transfer and Detection of Single Electrons Using Metal-Oxide-Semiconductor Field-Effect Transistors. IEICE Transactions on Electronics, 2007, E90-C, 943-948.	0.6	5
102	A High-Density Ternary Content-Addressable Memory Using Single-Electron Transistors. , 2006, , .		4
103	Studies on Metal-oxide-Semiconductor Field-Effect Transistor Low-Frequency Noise for Electrometer Applications. Japanese Journal of Applied Physics, 2006, 45, 3606-3608.	1.5	4
104	Molecular-Mediated Single-Electron Devices Operating at Room Temperature. Japanese Journal of Applied Physics, 2006, 45, 4285-4289.	1.5	6
105	Room-temperature-operating data processing circuit based on single-electron transfer and detection with metal-oxide-semiconductor field-effect transistor technology. Applied Physics Letters, 2006, 88, 183101.	3.3	64
106	Electrostatically gated Si devices: Coulomb blockade and barrier capacitance. Applied Physics Letters, 2006, 89, 052102.	3.3	13
107	Single electron tunneling transistor with tunable barriers using silicon nanowire metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2006, 88, 053121.	3.3	111
108	Single-electron device using Si nanodot array and multi-input gates. , 2006, , .		3

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109	Quantum effects in the capacitance between a pair of thin and slightly separated SrTiO ₃ slabs: A first-principles study. <i>Physical Review B</i> , 2006, 74, .	3.2	9
110	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and 295 K. <i>Physical Review B</i> , 2006, 74, .	3.2	15
111	Fast All-Optical Pulse Train Modulation by Silicon Photonic Crystal Nanocavities. , 2006, , .		1
112	Special Section on Novel Device Architectures and System Integration Technologies. <i>IEICE Transactions on Electronics</i> , 2006, E89-C, 1491-1491.	0.6	0
113	Charge-State Control of Phosphorus Donors in Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 2588-2591.	1.5	9
114	Back-Gate Effect on Coulomb Blockade in Silicon-on-Insulator Trench Wires. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 7717-7719.	1.5	8
115	Foundry Metal-oxide-semiconductor Field-Effect-Transistor Electrometer for Single-Electron Detection. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 4855-4858.	1.5	7
116	Charge-Injection Effects in a Single 4,4''-Terphenyldithiol Molecule. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 8759-8763.	1.5	6
117	Silicon Single-Electron Pump and Turnstile: Interplay with Crystalline Imperfections. <i>Materials Research Society Symposia Proceedings</i> , 2005, 864, 671.	0.1	1
118	Metal-semiconductor Transition in Single-Walled Carbon Nanotubes Induced by Low-Energy Electron Irradiation. <i>Nano Letters</i> , 2005, 5, 1575-1579.	9.1	87
119	Manipulation and detection of single electrons for future information processing. <i>Journal of Applied Physics</i> , 2005, 97, 031101.	2.5	112
120	First-Principles Study of Field-Effect Doping in Nano-Scale Systems by the Enforced Fermi-Energy Difference Method. <i>E-Journal of Surface Science and Nanotechnology</i> , 2005, 3, 453-456.	0.4	3
121	Simultaneous-Sweep Method for Evaluation of Single-Electron Transistors with Barriers Induced by Gate Electric Field. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L1048-L1050.	1.5	8
122	Analysis of Back-Gate Voltage Dependence of Threshold Voltage of Thin Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor and Its Application to Si Single-Electron Transistor. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 2036-2040.	1.5	18
123	Multilevel memory using an electrically formed single-electron box. <i>Applied Physics Letters</i> , 2004, 85, 1277-1279.	3.3	31
124	Multilevel memory using single-electron turnstile. <i>Electronics Letters</i> , 2004, 40, 229.	1.0	14
125	Automatic Control of Oscillation Phase of a Single-Electron Transistor. <i>IEEE Electron Device Letters</i> , 2004, 25, 31-33.	3.9	8
126	A multiple-valued logic and memory with combined single-electron and metal-oxide-semiconductor transistors. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 462-470.	3.0	106

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127	A compact analytical model for asymmetric single-electron tunneling transistors. IEEE Transactions on Electron Devices, 2003, 50, 455-461.	3.0	89
128	Correction to "A compact analytical model for asymmetric single-electron tunneling transistors". IEEE Transactions on Electron Devices, 2003, 50, 862-862.	3.0	1
129	Development of silicon single-electron devices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 95-101.	2.7	7
130	A Merged Single-Electron Transistor and Metal-Oxide-Semiconductor Transistor Logic for Interface and Multiple-Valued Functions. Japanese Journal of Applied Physics, 2002, 41, 2566-2568.	1.5	25
131	Silicon single-electron devices. Journal of Physics Condensed Matter, 2002, 14, R995-R1033.	1.8	111
132	Binary adders of multigate single-electron transistors: specific design using pass-transistor logic. IEEE Nanotechnology Magazine, 2002, 1, 93-99.	2.0	40
133	Silicon Single-Electron Transistors and Single-Electron CCD. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
134	Multipeak negative-differential-resistance device by combining single-electron and metal-oxide-semiconductor transistors. Applied Physics Letters, 2001, 79, 3618-3620.	3.3	49
135	A 0.5-V MTCMOS/SIMOX logic gate. IEEE Journal of Solid-State Circuits, 1997, 32, 1604-1609.	5.4	20
136	Nitrogen in-situ doped poly buffer LOCOS: simple and scalable isolation technology for deep-submicron silicon devices. IEEE Transactions on Electron Devices, 1996, 43, 311-317.	3.0	7
137	Evaluation of a copper metallization process and the electrical characteristics of copper-interconnected quarter-micron CMOS. IEEE Transactions on Electron Devices, 1996, 43, 1206-1212.	3.0	51
138	A 4:1 MUX Circuit Using 1/4 Micron CMOS/SIMOX for High-Speed and Low-Power Applications. Japanese Journal of Applied Physics, 1996, 35, 902-905.	1.5	1
139	Sub-1/4-µm dual-gate CMOS technology using in-situ doped polysilicon for nMOS and pMOS gates. IEEE Transactions on Electron Devices, 1995, 42, 1583-1590.	3.0	8
140	Sub-1/4 µm Dual Gate CMOS Technology using In Situ Doped Polysilicons for N and PMOS Gates. , 1993, , .		1
141	Degradation and Recovery of Metal-Oxide-Semiconductor (MOS) Devices Stressed with Fowler-Nordheim (FN) Gate Current. Japanese Journal of Applied Physics, 1991, 30, 1931-1936.	1.5	4
142	Direct Determination of Interface Trapped Charges. Japanese Journal of Applied Physics, 1991, 30, L888-L890.	1.5	1
143	Electrical characterization of metal-insulator-semiconductor diodes fabricated from laser-ablated YBa ₂ Cu ₃ O _{7-x} yttria-stabilized zirconia films on Si substrates. Applied Physics Letters, 1991, 59, 2889-2891.	3.3	20
144	Titanium silicide and titanium nitride formation by titanium-ion implantation for MOS LSI applications. Journal of Materials Research, 1991, 6, 1238-1247.	2.6	17

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145	Electrical Characterization of YBCO/YSZ/Si Diodes. , 1991, , .		0
146	A Complete Self-aligned-gate LID-MOS Technology. , 1988, , .		0
147	Film and interface properties of epitaxial metal/insulator/semiconductor systems formed by ionized cluster beam deposition. Surface Science, 1986, 168, 365-375.	1.9	13
148	Submicron MOSFETs with S/D Diffusions on a Field Insulator. , 1986, , .		1
149	Aluminium epitaxy on Si(111) and Si(100) using an ionized cluster beam. Thin Solid Films, 1985, 124, 179-184.	1.8	22
150	Al metallization by ionized-cluster beam deposition and epitaxy. Nuclear Instruments & Methods in Physics Research B, 1985, 7-8, 900-905.	1.4	8
151	Film deposition and buried layer formation by mass-analyzed ion beams. Nuclear Instruments & Methods in Physics Research B, 1985, 6, 439-446.	1.4	19
152	Observation of Initial Stage of Al Epitaxial Growth on Si(111) by Ionized Cluster Beam Deposition. Japanese Journal of Applied Physics, 1985, 24, L173-L174.	1.5	18
153	Ion beam deposition. Microelectronic Engineering, 1984, 2, 113-120.	2.4	0
154	Epitaxial growth of Al on Si(111) and Si(100) by ionized cluster beam. Journal of Applied Physics, 1984, 56, 2746-2750.	2.5	174
155	Vaporized-metal cluster formation and effect of kinetic energy of ionized clusters on film formation. Thin Solid Films, 1982, 92, 137-146.	1.8	47
156	A multiple-valued single-electron SRAM by the PADOX process. , 0, , .		5
157	Automatic control of the oscillation phase of a single-electron transistor by a memory node with a small MOSFET. , 0, , .		0
158	Silicon nano-devices and single-electron devices. , 0, , .		1
159	High-Efficiency SOI Photodetector Utilizing Surface Plasmon Resonance in Gold Corrugated Structure. Advanced Materials Research, 0, 222, 154-157.	0.3	1
160	Investigation of Adhesion Materials for Gold Line-and-Space Surface Plasmon Antenna on SOI-MOS Photodiode. Advanced Materials Research, 0, 222, 201-204.	0.3	2
161	Identification of double quantum dots in nanowire devices by single-gate sweeps. , 0, , .		1
162	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. , 0, , 131-139.		0